

MOSFET – Power, P-Channel, SOT-23

-20 V, -1.3 A

NTR1P02L, NVTR01P02L

These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

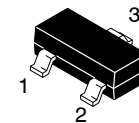
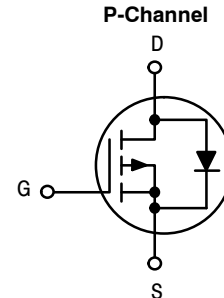
- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- NVTR Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free and Halide-Free Packages are Available

MAXIMUM RATINGS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-20	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 12	V
Drain Current			
– Continuous @ $T_A = 25\text{ }^\circ\text{C}$	I_D	-1.3	A
– Pulsed Drain Current ($t_p \leq 10\text{ }\mu\text{s}$)	I_{DM}	-4.0	A
Total Power Dissipation @ $T_A = 25\text{ }^\circ\text{C}$	P_D	400	mW
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	300	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

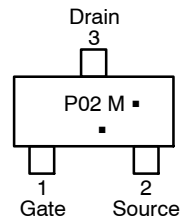
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
-20 V	220 m Ω @ -4.5 V	-1.3 A



SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM & PIN ASSIGNMENT



- P02 = Specific Device Code
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

* Date Code orientation may vary depending upon manufacturing location

ORDERING INFORMATION

Device	Package	Shipping†
NTR1P02LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
NTR1P02LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel
NVTR01P02LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$(V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A})$	$V_{(BR)DSS}$	-20			V
Zero Gate Voltage Drain Current	$(V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V})$ $(V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C})$	I_{DSS}			-1.0 -10	μA
Gate-Body Leakage Current	$(V_{GS} = \pm 12\text{ V}, V_{DS} = 0\text{ V})$	I_{GSS}			± 100	nA

ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage	$(V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A})$	$V_{GS(th)}$	-0.7	-1.0	-1.25	V
Static Drain-to-Source On-Resistance	$(V_{GS} = -4.5\text{ V}, I_D = -0.75\text{ A})$ $(V_{GS} = -2.5\text{ V}, I_D = -0.5\text{ A})$	$r_{DS(on)}$		0.140 0.200	0.22 0.35	Ω

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = -5.0\text{ V})$	C_{iss}		225		pF
Output Capacitance	$(V_{DS} = -5.0\text{ V})$	C_{oss}		130		
Transfer Capacitance	$(V_{DS} = -5.0\text{ V})$	C_{rss}		55		

SWITCHING CHARACTERISTICS (Note 2)

Turn-On Delay Time	$(V_{GS} = -4.5\text{ V}, V_{DD} = -5.0\text{ V}, I_D = -1.0\text{ A}, R_L = 5.0\text{ }\Omega, R_G = 6.0\text{ }\Omega)$	$t_{d(on)}$		7.0		ns
Rise Time		t_r		15		
Turn-Off Delay Time		$t_{d(off)}$		18		
Fall Time		t_f		9		
Total Gate Charge	$(V_{DS} = -16\text{ V}, I_D = -1.5\text{ A}, V_{GS} = -4.5\text{ V})$	Q_T		3.1		nC

SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Current		I_S			-0.6	A
Pulsed Current		I_{SM}			-0.75	
Forward Voltage (Note 2)	$(V_{GS} = 0\text{ V}, I_S = -0.6\text{ A})$	V_{SD}			-1.0	V
Reverse Recovery Time	$(I_S = -1.0\text{ A}, V_{GS} = 0\text{ V}, di_S/dt = 100\text{ A}/\mu\text{s})$	t_{rr}		16		ns
		t_a		11		
		t_b		5.5		
Reverse Recovery Stored Charge		Q_{RR}		8.5		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
2. Switching characteristics are independent of operating junction temperature.

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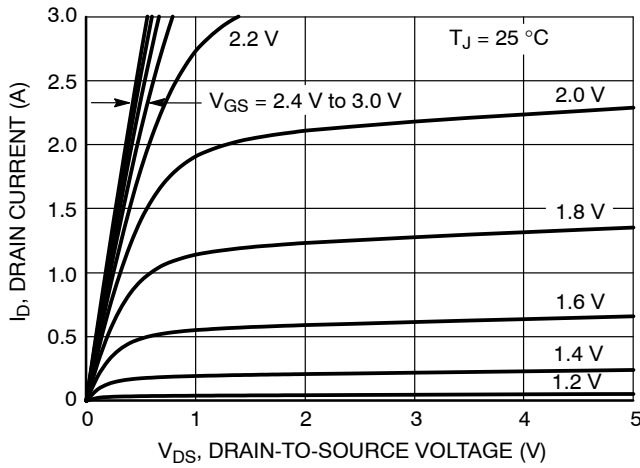


Figure 1. On-Region Characteristics

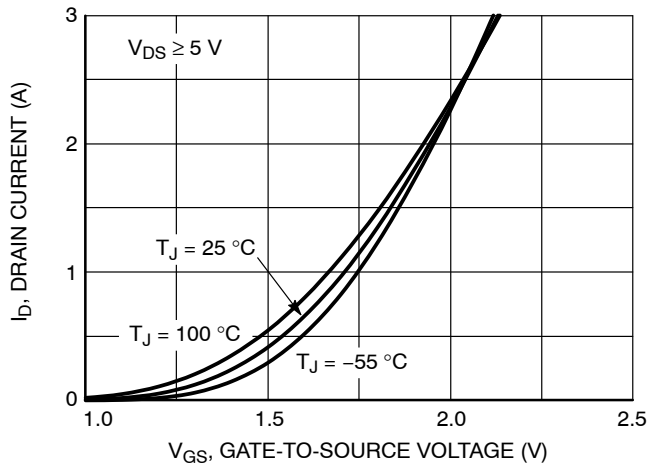


Figure 2. Transfer Characteristics

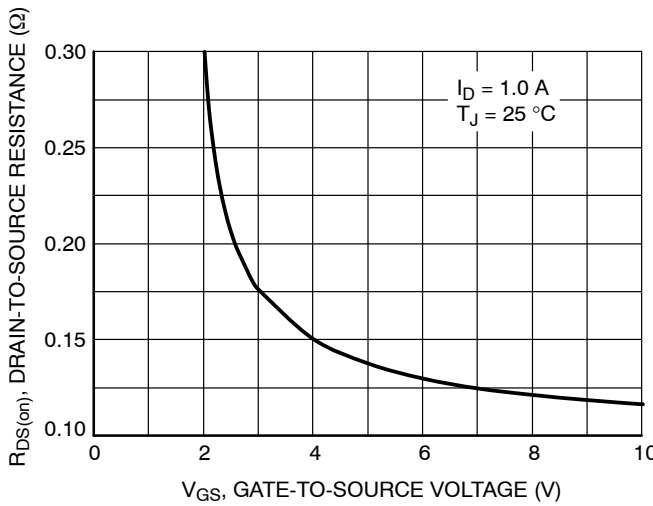


Figure 3. On-Resistance vs. Gate-to-Source Voltage

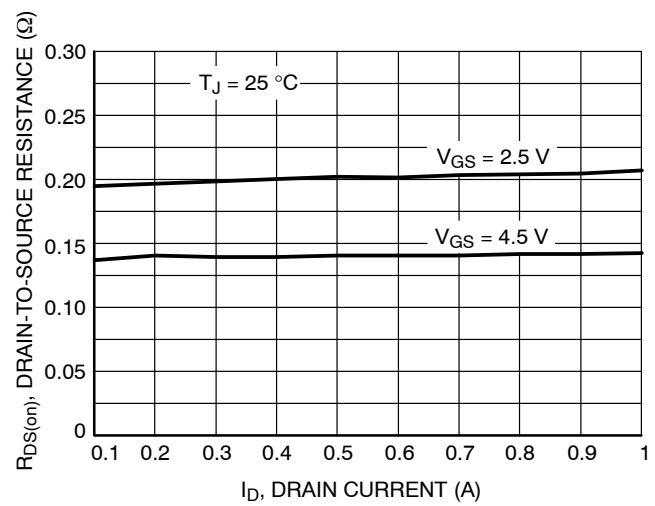


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

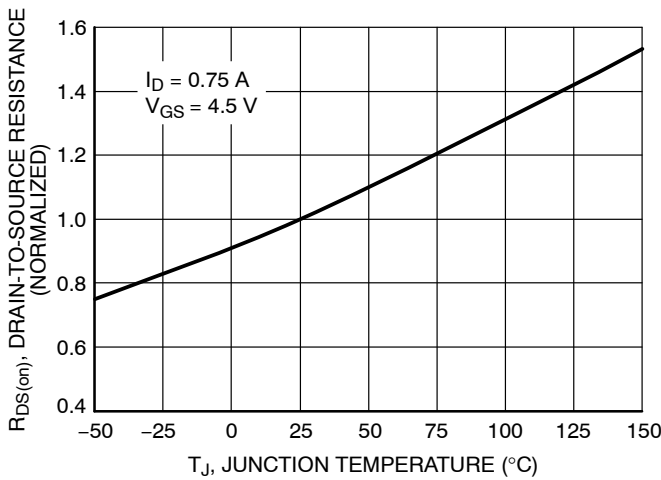


Figure 5. On-Resistance Variation with Temperature

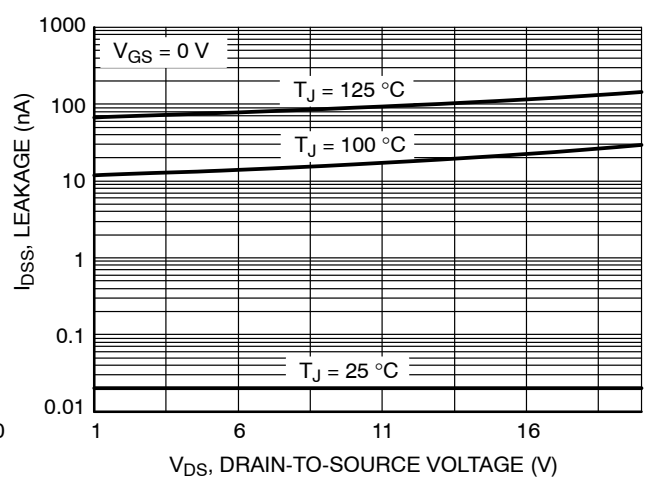


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTR1P02L, NVTR01P02L

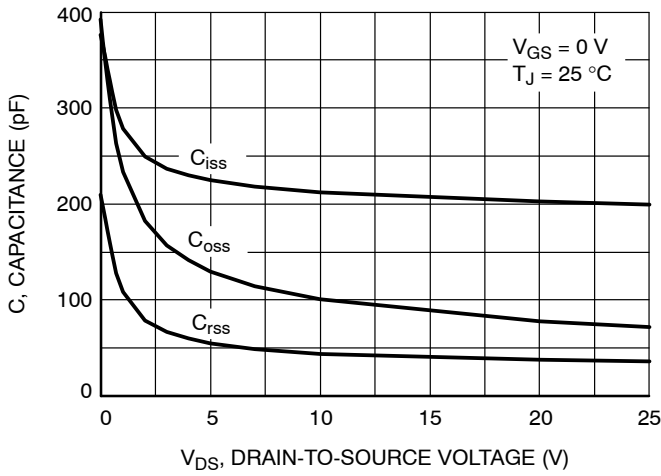


Figure 7. Capacitance Variation

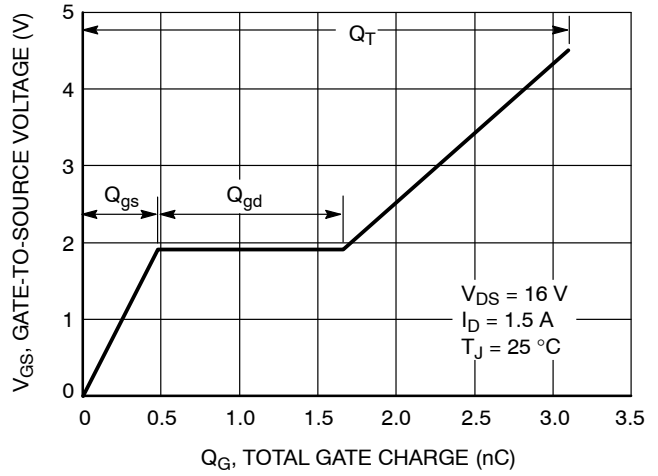


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

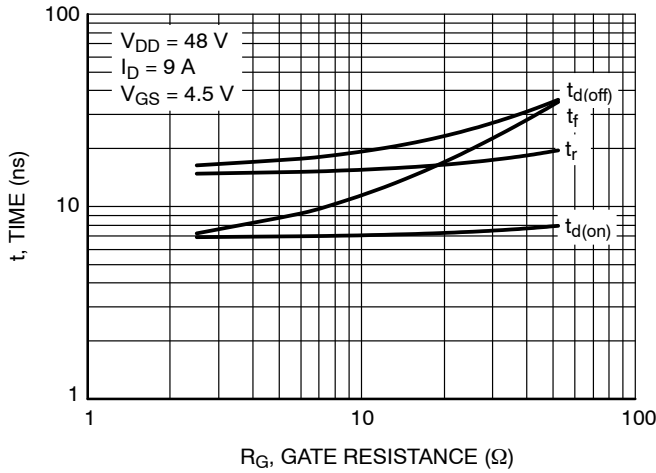


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

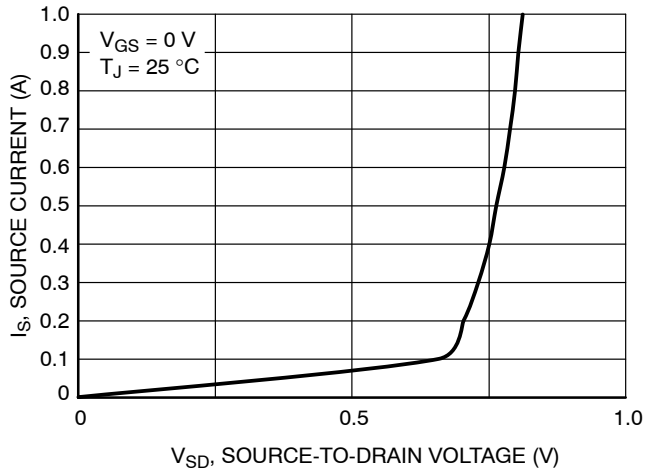


Figure 10. Diode Forward Voltage vs. Current

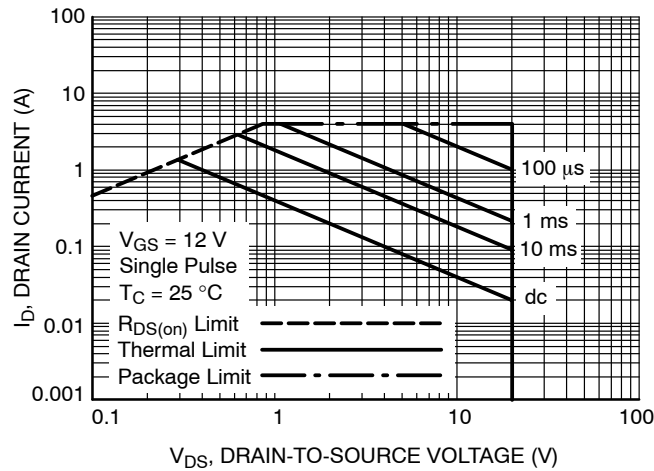


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTR1P02L, NVTR01P02L

REVISION HISTORY

Revision	Description of Changes	Date
15	Document rebranded to onsemi format.	1/23/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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